

**IN THE SPECIFICATION:**

Please amend paragraph [0040] as follows:

[0040] Since the desired leakage current does [[dose]] not flow at the off voltage  $V_{off}$  of the TFT, it is preferable that the alignment voltage source 63 supplies an electric field alignment voltage set at a voltage between the threshold voltage  $V_{th}$  of the TFT and the off voltage  $V_{off}$  of the TFT to the gate lines G1 to Gn. Specifically, since the leakage current of the TFT is very small below 0V and a shock applied to integrated circuit device of the alignment voltage source 63 becomes large above 1V, it is preferable that the voltage supplied to the gate lines G1 to Gn from the alignment voltage source during ferroelectric electric field alignment period is set at about 0 volt to about 1 volt. In other words, it is preferable that the voltage supplied to the gate lines G1 to Gn during electric field alignment period of the ferroelectric liquid crystal is set as about 0%~5% of the threshold voltage  $V_{th}$  of the TFT so as not to overload the TFT when the field voltage is applied.